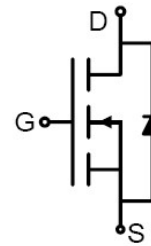


AP1002

N-Channel Enhancement Mosfet

Feature

- 100V,2A
 $R_{DS(ON)} < 273m\Omega @ V_{GS}=10V$ TYP:210 m Ω
 $R_{DS(ON)} < 338m\Omega @ V_{GS}=4.5V$ TYP:260 m Ω
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
1002	AP1002	SOT-23	7 inch	-	3000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	2	A
Continuous Drain Current ($T_a=100^{\circ}C$)	I_D	1.3	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	8	A
Power Dissipation	P_D	2.3	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	54	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽²⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.8	1.3	2.0	V
Drain-source on-resistance ⁽²⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$	-	210	273	m Ω
		$V_{GS} = 4.5V, I_D = 1A$	-	260	338	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	-	113	-	pF
Output Capacitance	C_{oss}		-	49.6	-	
Reverse Transfer Capacitance	C_{rss}		-	6	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, I_D = 2A, V_{GS} = 10V, R_G = 2\Omega$	-	4.6	-	ns
Turn-on rise time	t_r		-	5.5	-	
Turn-off delay time	$t_{d(off)}$		-	24.9	-	
Turn-off fall time	t_f		-	10.5	-	
Total Gate Charge	Q_g	$V_{DS} = 50V, I_D = 2A, V_{GS} = 10V$	-	3.0	-	nC
Gate-Source Charge	Q_{gs}		-	0.6	-	
Gate-Drain Charge	Q_{gd}		-	0.82	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V_{DS}	$V_{GS} = 0V, I_S = 1A$	-	-	1.2	V
Diode Forward current ⁽³⁾	I_S		-	-	1	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

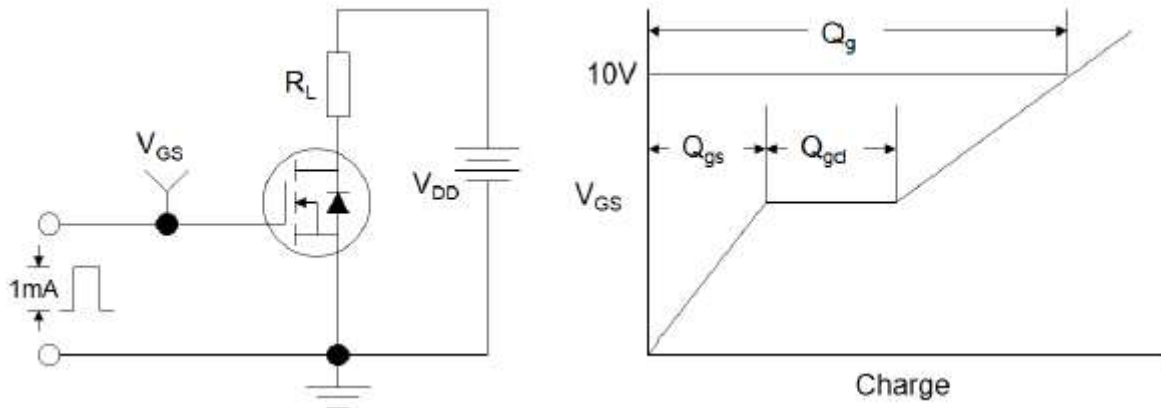


Figure1:Gate Charge Test Circuit & Waveform

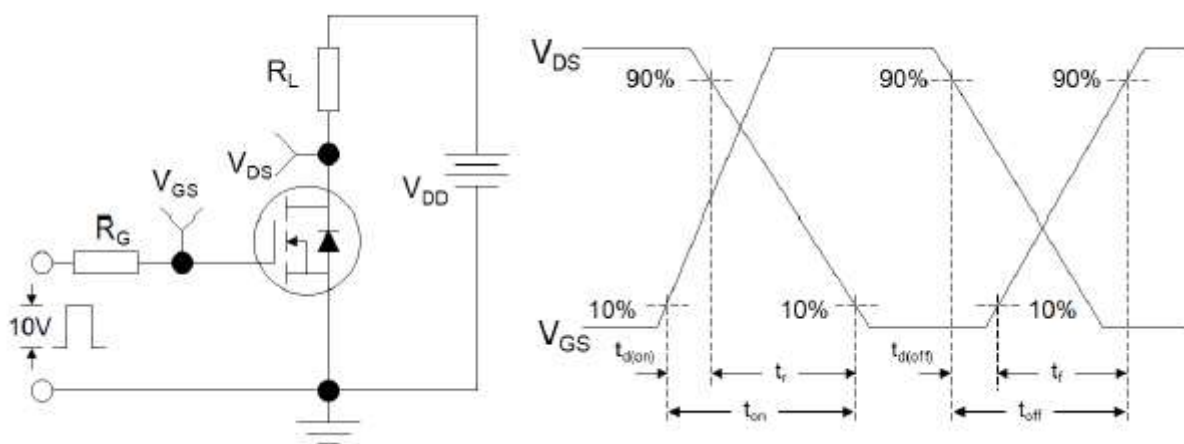


Figure 2: Resistive Switching Test Circuit & Waveforms

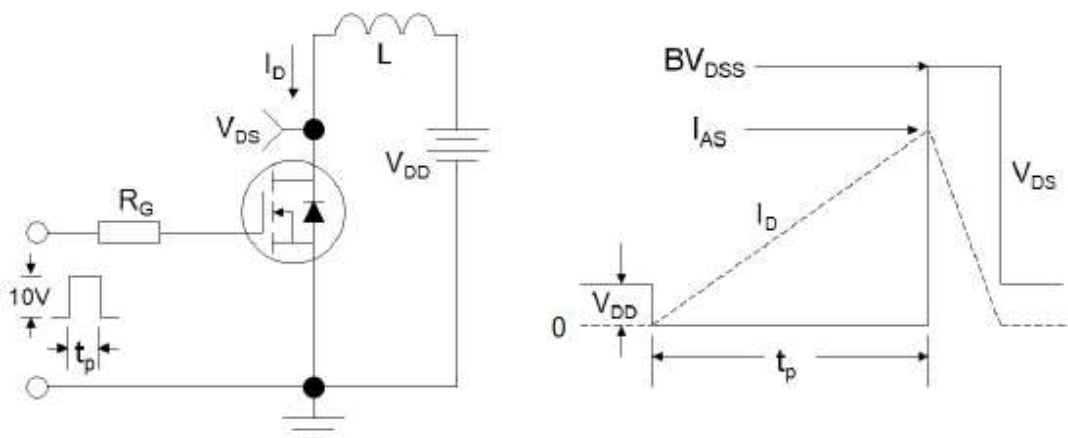


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

Figure 1: Output Characteristics

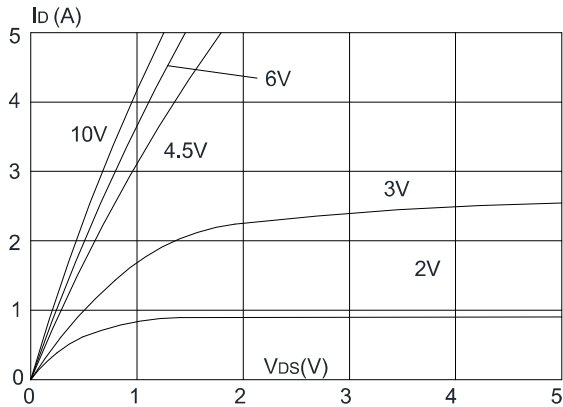


Figure 2: Typical Transfer Characteristics

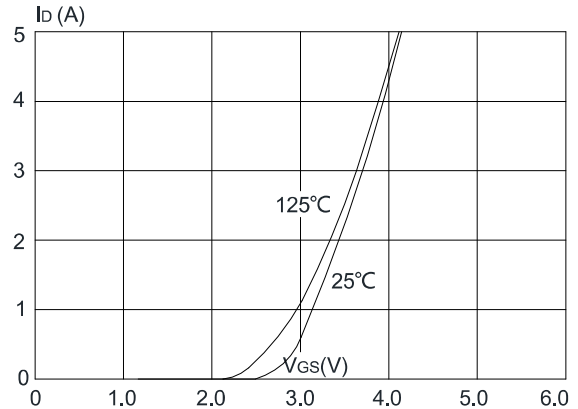


Figure 3: On-resistance vs. Drain Current

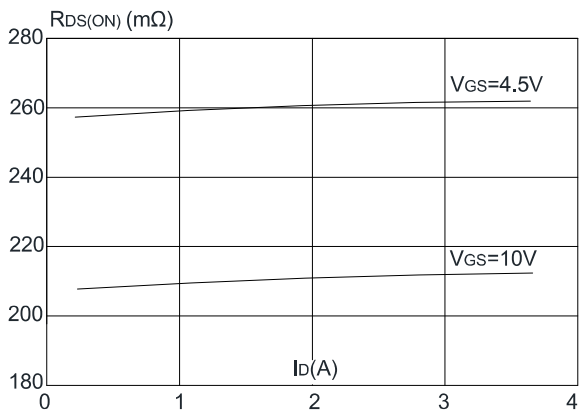


Figure 4: Body Diode Characteristics

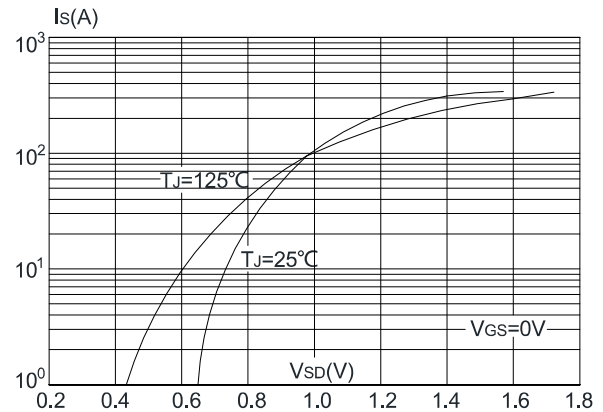


Figure 5: Gate Charge Characteristics

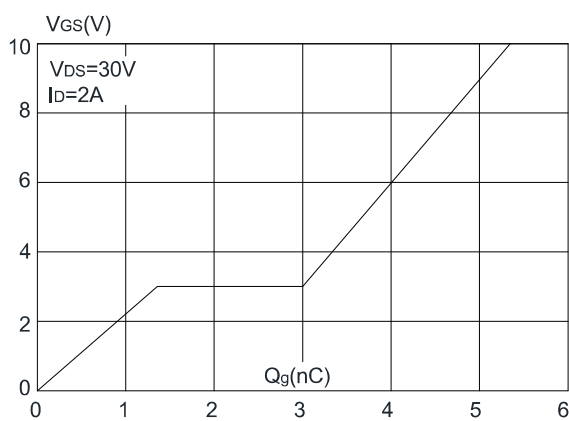
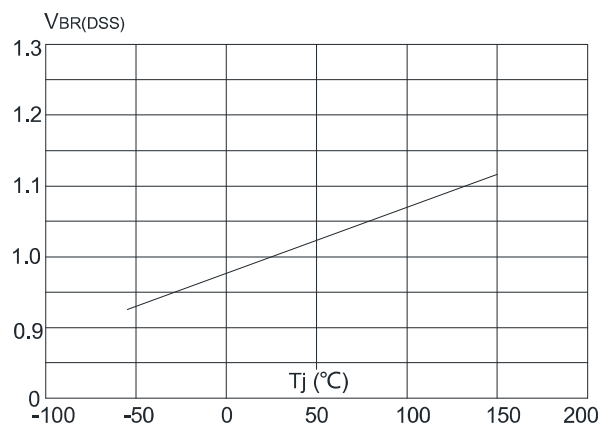


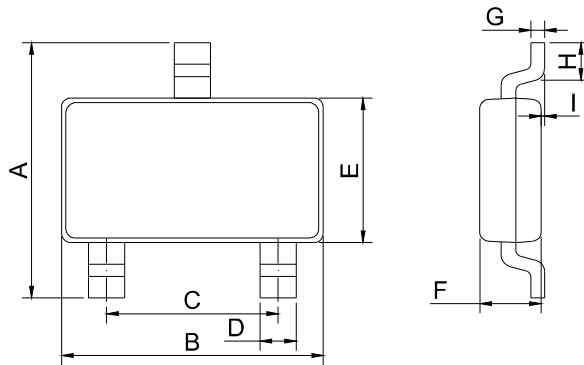
Figure 6: Normalized Breakdown Voltage vs. Junction Temperature



AP1002

N-Channel Enhancement Mosfet

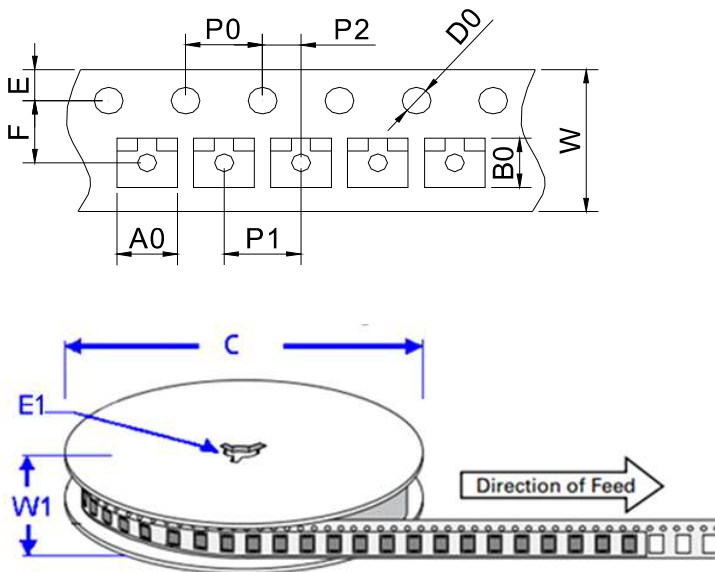
SOT-23 Package Information



SOT-23

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039